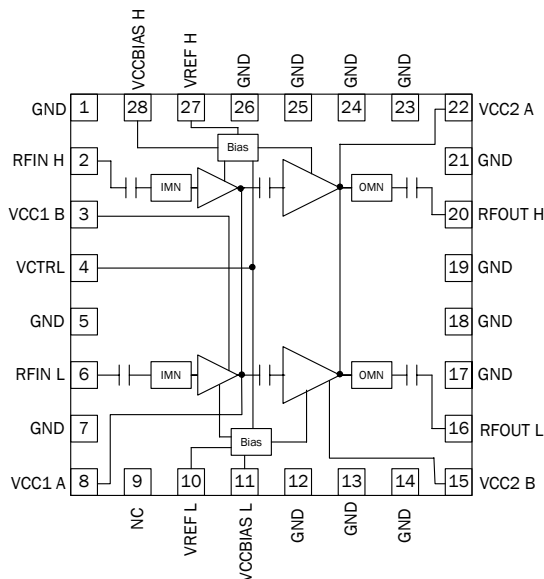


**Features**

- Multiple Band Coverage (Band I, II, III, IV, V, VI, VIII, IX)
- Input/Output Internally Matched@50Ω
- Up to 27dBm Linear Output-Power (HSDPA)
- 37% Peak Linear Efficiency (ULRMC 12.2Kbps)
- 25% Linear Efficiency at 16dBm
- -40dBc ACLR @ ±5MHz
- Analog Bias Control
- Load Insensitive

**Applications**

- 3V UMTS Multi-Band Handsets
- Multi-Mode UMTS Handsets
- Spread-Spectrum Systems



Functional Block Diagram

**Product Description**

The RF6285 is a high-power, high-efficiency multi-band linear amplifier module specifically designed for 3V handheld systems. This amplifier uses a balanced architecture which makes the PA load insensitive and therefore eliminates the need for isolators. The device is manufactured on an advanced eighth generation GaAs HBT process, and was designed for use as the final RF amplifier in 3V UMTS handheld digital cellular equipment, spread-spectrum systems, and other applications in the 824MHz to 915MHz and 1710MHz to 1980MHz band. The RF6285 has an analog bias control pin to reduce idle current at low power levels. The RF6285 is assembled in a 28-pin, 5.5 mm x 6.0 mm, laminate package.

**Ordering Information**

RF6285                      3V Multi-Band UMTS Linear Power Amplifier Module  
RF6285PCBA-41X       Fully Assembled Evaluation Board

**Optimum Technology Matching® Applied**

- |  |                                      |                                     |                                   |
|--|--------------------------------------|-------------------------------------|-----------------------------------|
| <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET         | <input type="checkbox"/> Si BiCMOS   | <input type="checkbox"/> Si CMOS    |                                   |
| <input type="checkbox"/> InGaP HBT           | <input type="checkbox"/> SiGe HBT    | <input type="checkbox"/> Si BJT     |                                   |

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## Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage (RF off)	+7.0	V
Supply Voltage ( $P_{OUT} \leq 29\text{dBm}$ )	+4.5	V
Reference Control Voltage ( $V_{REF}$ )	+3.6	V
Input RF Power	+6.0	dBm
ABC Voltage ( $V_{CTRL}$ )	+2.3	V
Operating Temperature	-30 to +100	°C
Storage Temperature	-40 to +150	°C
Moisture Sensitivity Level (IPC/JEDEC J-STD-20)	MSL3@260	°C



**Caution!** ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective2002/95/EC (at time of this document revision).

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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Low Band RF</b>					
<b>Band VIII High Power</b>					T = 25 °C Ambient, $V_{CC} = 3.1\text{V}$ , $V_{CCBIAS} = 3.1\text{V}$ , $V_{REF} = 2.85\text{V}$ , $V_{CTRL} = 1.95\text{V}$ , $R_L = 50\Omega$ , and $P_{OUT} = 27\text{dBm}$ for all parameters (unless otherwise specified). Modulation is HSDPA.
Operating Frequency Range	880		915	MHz	
Linear Gain		28		dB	
Gain Variation into Mismatch		±1		dB	VSWR is 1:1 out to 3:1, all phase angles
Harmonics		-19	-10	dBm	$f = 2f_0, 3f_0$
Maximum Linear Output	27			dBm	
Linear Efficiency		37		%	UL RMC, 12.2Kbps, $V_{CC} = 2.8\text{V}$
Maximum $I_{CC}$		490		mA	
ACLR1 @ ±5MHz		-39		dBc	
ACLR2 @ ±10MHz		-55		dBc	
ACLR @ ±5MHz into Mismatch		-36		dBc	VSWR is 1:1 out to 3:1, all phase angles
ACLR @ ±10MHz into Mismatch		-46		dBc	VSWR is 1:1 out to 3:1, all phase angles
Input Return Loss			-12	dB	
Output Load VSWR Stability (Spurious Emissions)			-46	dBc	VSWR = 6:1
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR = 10:1
Noise Power		-136		dBm/Hz	$-50 \leq P_{OUT} \leq +27\text{dBm}$ , RX = 470MHz to 770MHz
		-133		dBm/Hz	$-50 \leq P_{OUT} \leq +27\text{dBm}$ , RX = 925MHz to 960MHz (Band VIII WRX = WTX + 45MHz)
		-153		dBm/Hz	$-50 \leq P_{OUT} \leq +27\text{dBm}$ , RX = 1570MHz to 1580MHz (GPS)
		-150		dBm/Hz	$-50 \leq P_{OUT} \leq +27\text{dBm}$ , RX = 1805MHz to 1880MHz (Band III and IX)
		-160		dBm/Hz	$-50 \leq P_{OUT} \leq +27\text{dBm}$ , RX = 1930MHz to 1990MHz (Band II)
		-160		dBm/Hz	$-50 \leq P_{OUT} \leq +27\text{dBm}$ , RX = 2110MHz to 2170MHz (Band I)
		-160		dBm/Hz	$-50 \leq P_{OUT} \leq +27\text{dBm}$ , RX = 2400MHz to 2480MHz (Bluetooth)

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Band VIII High Power, cont.</b>					
Reverse IM Products					
IM 5MHz			-31	dBc	IF offset $f_0 + 5$ MHz with CW signal = -40 dBc
IM 10MHz			-41	dBc	IF offset $f_0 + 10$ MHz with CW signal = -40 dBc
<b>Band VIII Medium Power</b>					
T = 25°C Ambient, $V_{CC} = 1.2$ V, $V_{CCBIAS} = 3.1$ V, $V_{REF} = 2.85$ V, $V_{CTRL} = 1.6$ V, $R_L = 50\Omega$ , and $P_{OUT} = 16$ dBm for all parameters (unless otherwise specified). Modulation is HSDPA.					
Linear Gain		22		dB	
Maximum Linear Output	16			dBm	
Linear Efficiency		23		%	
Maximum $I_{CC}$		150		mA	
ACLR @ $\pm 5$ MHz		-40		dBc	
ACLR @ $\pm 10$ MHz		-56		dBc	
Input Return Loss			-12	dB	
Output Load VSWR Stability (Spurious Emissions)			-46	dBc	VSWR = 6:1
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR = 10:1
Reverse IM Products					
IM 5MHz			-31	dBc	IF offset $f_0 + 5$ MHz with CW signal = -40 dBc
IM 10MHz			-41	dBc	IF offset $f_0 + 10$ MHz with CW signal = -40 dBc
<b>Band VIII Low Power</b>					
T = 25°C Ambient, $V_{CC} = 0.6$ V, $V_{CCBIAS} = 3.1$ V, $V_{REF} = 2.85$ V, $V_{CTRL} = 1.42$ V, $R_L = 50\Omega$ , and $P_{OUT} = 5$ dBm for all parameters (unless otherwise specified). Modulation is HSDPA.					
Linear Gain		17		dB	
Maximum Linear Output	5			dBm	
Linear Efficiency		10		%	
ACLR @ $\pm 5$ MHz		-40		dBc	
ACLR @ $\pm 10$ MHz		-58		dBc	
<b>Band V High Power</b>					
T = 25°C Ambient, $V_{CC} = 3.1$ V, $V_{CCBIAS} = 3.1$ V, $V_{REF} = 2.85$ V, $V_{CTRL} = 1.95$ V, $R_L = 50\Omega$ , and $P_{OUT} = 27$ dBm for all parameters (unless otherwise specified). Modulation is HSDPA.					
Operating Frequency Range	824		849	MHz	
Linear Gain		28		dB	
Gain Variation into Mismatch		-1, +0.5		dB	VSWR is 1:1 out to 3:1, all phase angles
Harmonics		-19	-10	dBm	$f = 2f_0, 3f_0$
Maximum Linear Output	27			dBm	
Linear Efficiency		36		%	UL RMC, 12.2 Kbps, $V_{CC} = 2.8$ V
Maximum $I_{CC}$		505		mA	
ACLR1 @ $\pm 5$ MHz		-40		dBc	
ACLR2 @ $\pm 10$ MHz		-56		dBc	
ACLR @ $\pm 5$ MHz into Mismatch		-36		dBc	VSWR is 1:1 out to 3:1, all phase angles
ACLR @ $\pm 10$ MHz into Mismatch		-46		dBc	VSWR is 1:1 out to 3:1, all phase angles
Input Return Loss			-12	dB	

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Band V High Power, cont.</b>					
Output Load VSWR Stability (Spurious Emissions)			-46	dBc	VSWR=6:1
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR=10:1
Noise Power		-135		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=470MHz to 770MHz
		-135		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=869MHz to 894MHz (Band V WRX=WTX+45MHz)
		-153		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=1570MHz to 1580MHz (GPS)
		-157		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=1805MHz to 1880MHz (Band III and IX)
		-161		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=1930MHz to 1990MHz (Band II)
		-163		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=2110MHz to 2170MHz (Band I)
		-164		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=2400MHz to 2480MHz (Bluetooth)
Reverse IM Products					
IM 5MHz			-31	dBc	IF offset $f_0 + 5$ MHz with CW signal=-40dBc
IM 10MHz			-41	dBc	IF offset $f_0 + 10$ MHz with CW signal=-40dBc
<b>Band V Medium Power</b>					
Linear Gain		22		dB	
Maximum Linear Output	16			dBm	
Linear Efficiency		22		%	
Maximum $I_{CC}$		150		mA	
ACLR @ $\pm 5$ MHz		-40		dBc	
ACLR @ $\pm 10$ MHz		-57		dBc	
Input Return Loss			-12	dB	
Output Load VSWR Stability (Spurious Emissions)			-46	dBc	VSWR=6:1
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR=10:1
Reverse IM Products					
IM 5MHz			-31	dBc	IF offset $f_0 + 5$ MHz with CW signal=-40dBc
IM 10MHz			-41	dBc	IF offset $f_0 + 10$ MHz with CW signal=-40dBc
<b>Band V Low Power</b>					
Linear Gain		15		dB	
Maximum Linear Output	5			dBm	
Linear Efficiency		10		%	
ACLR @ $\pm 5$ MHz		-40		dBc	
ACLR @ $\pm 10$ MHz		-58		dBc	

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Power Supply (Low Band)</b>					
Supply Voltage ( $V_{CC1}$ and $V_{CC2}$ )	3.1	3.4	4.3	V	Full rated power.
	0.6			V	Low power with DC to DC Converter
$V_{CC}$ Bias	2.9		4.3	V	
High Power Idle Current ( $I_{CC1}/I_{CC2}/I_{CCBIAS}$ )		120		mA	$V_{CC}=3.1V$ , $V_{CTRL}=1.95V$ and $V_{REF}=2.85V$
Low Power Idle Current ( $I_{CC1}/I_{CC2}/I_{CCBIAS}$ )		35		mA	$V_{CC}=0.6V$ , $V_{CTRL}=1.42V$ and $V_{REF}=2.85V$
$V_{REF}$ Current		2		mA	
$V_{CTRL}$ Current		300		uA	
RF Turn On/Off Time		1.2		uS	
DC Turn On/Off Time		2		uS	
Total Current (Power Down)		0.2		uA	
$V_{REF}$ Low Voltage (Power Down)	0		0.5	V	
$V_{REF}$ High Voltage (Recommended)	2.75	2.85	2.95	V	
$V_{CTRL}$ Voltage Range	1.0		2.4	V	Higher output power requires higher $V_{CTRL}$ voltage

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
High Band RF					
Band I High Power					T=25°C Ambient, V <sub>CC</sub> =3.1V, V <sub>CCBIAS</sub> =3.1V, V <sub>REF</sub> =2.85V, V <sub>CTRL</sub> =1.95V, R <sub>L</sub> =50Ω, and P <sub>OUT</sub> =27dBm for all parameters (unless otherwise specified). Modulation is HSDPA.
Operating Frequency Range	1920		1980	MHz	
Linear Gain		28		dB	
Gain Variation into Mismatch		-1, +0.5		dB	VSWR is 1:1 out to 3:1, all phase angles
Harmonics		-19	-10	dBm	f=2f <sub>0</sub> , 3f <sub>0</sub>
Maximum Linear Output	27			dBm	
Linear Efficiency		35		%	UL RMC, 12.2Kbps, V <sub>CC</sub> =2.8V
Maximum I <sub>CC</sub>		505		mA	
ACLR1 @ ±5MHz		-39		dBc	
ACLR2 @ ±10MHz		-55		dBc	
ACLR @ ±5MHz into Mismatch		-36		dBc	VSWR is 1:1 out to 3:1, all phase angles
ACLR @ ±10MHz into Mismatch		-46		dBc	VSWR is 1:1 out to 3:1, all phase angles
Input Return Loss			-12	dB	
Output Load VSWR Stability (Spurious Emissions)			-46	dBc	VSWR=6:1
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR=10:1
Noise Power		-145		dBm/Hz	-50 ≤ P <sub>OUT</sub> ≤ +27 dBm, RX=470MHz to 770MHz
		-148		dBm/Hz	-50 ≤ P <sub>OUT</sub> ≤ +27 dBm, RX=869MHz to 960MHz (Band V, VI, VIII)
		-137		dBm/Hz	-50 ≤ P <sub>OUT</sub> ≤ +27 dBm, RX=1570MHz to 1580MHz (GPS)
		-128		dBm/Hz	-50 ≤ P <sub>OUT</sub> ≤ +27 dBm, RX=1805MHz to 1880MHz (Band III and IX)
		-138		dBm/Hz	-50 ≤ P <sub>OUT</sub> ≤ +27 dBm, RX=2110MHz to 2170MHz (Band I), TX/RX offset=130MHz to 190MHz
		-146		dBm/Hz	-50 ≤ P <sub>OUT</sub> ≤ +27 dBm, RX=2400MHz to 2480MHz (Bluetooth)
		-126		dBm/Hz	-50 ≤ P <sub>OUT</sub> ≤ +27 dBm, TX=1932.3MHz to 1980MHz, RX=1893.5MHz to 1919.6MHz (PHS)
Reverse IM Products					
IM 5MHz			-31	dBc	IF offset f <sub>0</sub> +5MHz with CW signal=-40dBc
IM 10MHz			-41	dBc	IF offset f <sub>0</sub> +10MHz with CW signal=-40dBc

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Band I Medium Power</b>					T = 25°C Ambient, V <sub>CC</sub> = 1.2V, V <sub>CCBIAS</sub> = 3.1V, V <sub>REF</sub> = 2.85V, V <sub>CTRL</sub> = 1.6V, R <sub>L</sub> = 50Ω, and P <sub>OUT</sub> = 16dBm for all parameters (unless otherwise specified). Modulation is HSDPA.
Linear Gain		22		dB	
Maximum Linear Output	16			dBm	
Linear Efficiency		20		%	
Maximum I <sub>CC</sub>		150		mA	
ACLR @ ±5MHz		-40		dBc	
ACLR @ ±10MHz		-55		dBc	
Input Return Loss			-12	dB	
Output Load VSWR Stability (Spurious Emissions)			-46	dBc	VSWR = 6:1
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR = 10:1
Reverse IM Products					
IM 5MHz			-31	dBc	IF offset f <sub>0</sub> + 5MHz with CW signal = -40dBc
IM 10MHz			-41	dBc	IF offset f <sub>0</sub> + 10MHz with CW signal = -40dBc
<b>Band I Low Power</b>					T = 25°C Ambient, V <sub>CC</sub> = 0.6V, V <sub>CCBIAS</sub> = 3.1V, V <sub>REF</sub> = 2.85V, V <sub>CTRL</sub> = 1.42V, R <sub>L</sub> = 50Ω, and P <sub>OUT</sub> = 5dBm for all parameters (unless otherwise specified). Modulation is HSDPA.
Linear Gain		15		dB	
Maximum Linear Output	5			dBm	
Linear Efficiency		10		%	
ACLR @ ±5MHz		-40		dBc	
ACLR @ ±10MHz		-58		dBc	
<b>Band II High Power</b>					T = 25 °C Ambient, V <sub>CC</sub> = 3.1V, V <sub>CCBIAS</sub> = 3.1V, V <sub>REF</sub> = 2.85V, V <sub>CTRL</sub> = 1.95V, R <sub>L</sub> = 50Ω, and P <sub>OUT</sub> = 27 dBm for all parameters (unless otherwise specified). Modulation is HSDPA.
Operating Frequency Range	1850		1910	MHz	
Linear Gain		28		dB	
Gain Variation into Mismatch		-1, +0.5		dB	VSWR is 1:1 out to 3:1, all phase angles
Harmonics		-19	-10	dBm	f = 2f <sub>0</sub> , 3f <sub>0</sub>
Maximum Linear Output	27			dBm	
Linear Efficiency		36		%	UL RMC, 12.2Kbps, V <sub>CC</sub> = 2.8V
Maximum I <sub>CC</sub>		505		mA	
ACLR1 @ ±5MHz		-39		dBc	
ACLR2 @ ±10MHz		-55		dBc	
ACLR @ ±5MHz into Mismatch		-36		dBc	VSWR is 1:1 out to 3:1, all phase angles
ACLR @ ±10MHz into Mismatch		-46		dBc	VSWR is 1:1 out to 3:1, all phase angles
Input Return Loss			-12	dB	
Output Load VSWR Stability (Spurious Emissions)			-46	dBc	VSWR = 6:1
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR = 10:1

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Band II High Power, cont.</b>					
Noise Power		-145		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=470 MHz to 770 MHz
		-150		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=869 MHz to 960 MHz (Band V, VI, VIII)
		-133		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=1570 MHz to 1580 MHz (GPS)
		-134		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=1930 MHz to 1990 MHz (Band II), TX/RX Offset=80 MHz
		-137		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=2110 MHz to 2170 MHz (Band I)
		-143		dBm/Hz	$-50 \leq P_{OUT} \leq +27$ dBm, RX=2400 MHz to 2480 MHz (Bluetooth)
Reverse IM Products					
IM 5 MHz			-31	dBc	IF offset $f_0 + 5$ MHz with CW signal = -40 dBc
IM 10 MHz			-41	dBc	IF offset $f_0 + 10$ MHz with CW signal = -40 dBc
<b>Band II Medium Power</b>					
T=25°C Ambient, $V_{CC}=1.2$ V, $V_{CCBIAS}=3.1$ V, $V_{REF}=2.85$ V, $V_{CTRL}=1.6$ V, $R_L=50\Omega$ , and $P_{OUT}=16$ dBm for all parameters (unless otherwise specified). Modulation is HSDPA.					
Linear Gain		22		dB	
Maximum Linear Output	16			dBm	
Linear Efficiency		22		%	
Maximum $I_{CC}$		150		mA	
ACLR @ $\pm 5$ MHz		-40		dBc	
ACLR @ $\pm 10$ MHz		-57		dBc	
Input Return Loss			-12	dB	
Output Load VSWR Stability (Spurious Emissions)			-46	dBc	VSWR=6:1
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR=10:1
Reverse IM Products					
IM 5 MHz			-31	dBc	IF offset $f_0 + 5$ MHz with CW signal = -40 dBc
IM 10 MHz			-41	dBc	IF offset $f_0 + 10$ MHz with CW signal = -40 dBc
<b>Band II Low Power</b>					
T=25°C Ambient, $V_{CC}=0.6$ V, $V_{CCBIAS}=3.1$ V, $V_{REF}=2.85$ V, $V_{CTRL}=1.42$ V, $R_L=50\Omega$ , and $P_{OUT}=5$ dBm for all parameters (unless otherwise specified). Modulation is HSDPA.					
Linear Gain		15		dB	
Maximum Linear Output	5			dBm	
Linear Efficiency		10		%	
ACLR @ $\pm 5$ MHz		-43		dBc	
ACLR @ $\pm 10$ MHz		-58		dBc	



Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Band III, IV High Power</b>					T=25°C Ambient, V <sub>CC</sub> =3.1V, V <sub>CCBIAS</sub> =3.1V, V <sub>REF</sub> =2.85V, V <sub>CTRL</sub> =2.1V, R <sub>L</sub> =50Ω, and P <sub>OUT</sub> =27dBm for all parameters (unless otherwise specified). Modulation is HSDPA.
Operating Frequency Range	1710		1785	MHz	
Linear Gain		28		dB	
Gain Variation into Mismatch		-2, +0.5		dB	VSWR is 1:1 out to 3:1, all phase angles
Harmonics		-19	-10	dBm	f=2f <sub>0</sub> , 3f <sub>0</sub>
Maximum Linear Output	27			dBm	
Linear Efficiency		33		%	UL RMC, 12.2Kbps, V <sub>CC</sub> =2.8V
Maximum I <sub>CC</sub>		542		mA	
ACLR1 @ ±5MHz		-39		dBc	
ACLR2 @ ±10MHz		-57		dBc	
ACLR @ ±5MHz into Mismatch		-34		dBc	VSWR is 1:1 out to 3:1, all phase angles
ACLR @ ±10MHz into Mismatch		-46		dBc	VSWR is 1:1 out to 3:1, all phase angles
Input Return Loss			-12	dB	
Output Load VSWR Stability (Spurious Emissions)			-46	dBc	VSWR=6:1
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR=10:1
Noise Power		-140		dBm/Hz	-50≤P <sub>OUT</sub> ≤+27dBm, RX=470MHz to 770MHz
		-140		dBm/Hz	-50≤P <sub>OUT</sub> ≤+27dBm, RX=869MHz to 960MHz (Band V)
		-131		dBm/Hz	-50≤P <sub>OUT</sub> ≤+27dBm, RX=1570MHz to 1580MHz (GPS)
		-134		dBm/Hz	-50≤P <sub>OUT</sub> ≤+27dBm, RX=1805MHz to 1880MHz (Band III and IX), TX/RX offset=95MHz
		-135		dBm/Hz	-50≤P <sub>OUT</sub> ≤+27dBm, RX=1930MHz to 1990MHz (Band II)
		-141		dBm/Hz	-50≤P <sub>OUT</sub> ≤+27dBm, RX=2110MHz to 2170MHz (Band I & IV)
		-146		dBm/Hz	-50≤P <sub>OUT</sub> ≤+27dBm, RX=2400MHz to 2480MHz (Bluetooth)
Reverse IM Products					
IM 5MHz			-31	dBc	IF offset f <sub>0</sub> +5MHz with CW signal=-40dBc
IM 10MHz			-41	dBc	IF offset f <sub>0</sub> +10MHz with CW signal=-40dBc
<b>Band III, IV Medium Power</b>					T=25°C Ambient, V <sub>CC</sub> =1.2V, V <sub>CCBIAS</sub> =3.1V, V <sub>REF</sub> =2.85V, V <sub>CTRL</sub> =1.6V, R <sub>L</sub> =50Ω, and P <sub>OUT</sub> =16dBm for all parameters (unless otherwise specified). Modulation is HSDPA.
Linear Gain		22		dB	
Maximum Linear Output	16			dBm	
Linear Efficiency		21		%	
Maximum I <sub>CC</sub>		158		mA	
ACLR @ ±5MHz		-40		dBc	
ACLR @ ±10MHz		-56		dBc	
Input Return Loss			-12	dB	

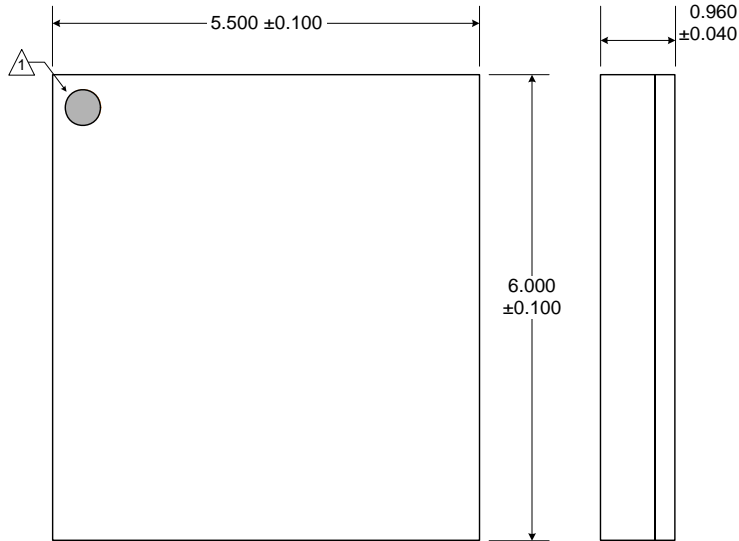
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Band III, IV Medium Power, cont.</b>					
Output Load VSWR Stability (Spurious Emissions)			-46	dBc	VSWR=6:1
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR=10:1
Reverse IM Products					
IM 5MHz			-31	dBc	IF offset $f_0 + 5$ MHz with CW signal=-40dBc
IM 10MHz			-41	dBc	IF offset $f_0 + 10$ MHz with CW signal=-40dBc
<b>Band III, IV Low Power</b>					
T=25°C Ambient, V <sub>CC</sub> =0.6V, V <sub>CCBIAS</sub> =3.1V, V <sub>REF</sub> =2.85V, V <sub>CTRL</sub> =1.44V, R <sub>L</sub> =50Ω, and P <sub>OUT</sub> =5dBm for all parameters (unless otherwise specified). Modulation is HSDPA.					
Linear Gain		15		dB	
Maximum Linear Output	5			dBm	
Linear Efficiency		9		%	
ACLR @ ±5MHz		-40		dBc	
ACLR @ ±10MHz		-58		dBc	
<b>Power Supply (High Band)</b>					
Supply Voltage (V <sub>CC1</sub> and V <sub>CC2</sub> )	3.1	3.4	4.3	V	Full rated power
	0.6			V	Low power with DC to DC Converter
V <sub>CC</sub> Bias	2.9		4.3	V	
High Power Idle Current (I <sub>CC1</sub> /I <sub>CC2</sub> /I <sub>CCBIAS</sub> )		130		mA	V <sub>CC</sub> =3.1V, V <sub>CTRL</sub> =1.95V, and V <sub>REF</sub> =2.85V
Low Power Idle Current (I <sub>CC1</sub> /I <sub>CC2</sub> /I <sub>CCBIAS</sub> )		35		mA	V <sub>CC</sub> =0.6V, V <sub>CTRL</sub> =1.42V, and V <sub>REF</sub> =2.85V
V <sub>REF</sub> Current		2		mA	
V <sub>CTRL</sub> Current		300		uA	
RF Turn On/Off Time		1.2		uS	
DC Turn On/Off Time		2		uS	
Total Current (Power Down)		0.2		uA	
V <sub>REF</sub> Low Voltage (Power Down)	0		0.5	V	
V <sub>REF</sub> High Voltage (Recommended)	2.75	2.85	2.95	V	
V <sub>CTRL</sub> Voltage Range	1.0		2.3	V	Higher output power requires higher V <sub>CTRL</sub> voltage

HSDPA Set-up: $\beta_{HS}/\beta_C=24/15$ , $\beta_C/\beta_D=12/15$	Settings	
1 DPCCH @ 15ksps	Spread Code=0	Relative Power=-7.095 dB
1 DPDCH @ 60ksps	Spread Code=16	Relative Power=-5.157 dB
1 DPCCH @ 15ksps	Spread Code=64	Relative Power=-3.012 dB

## Pin Descriptions

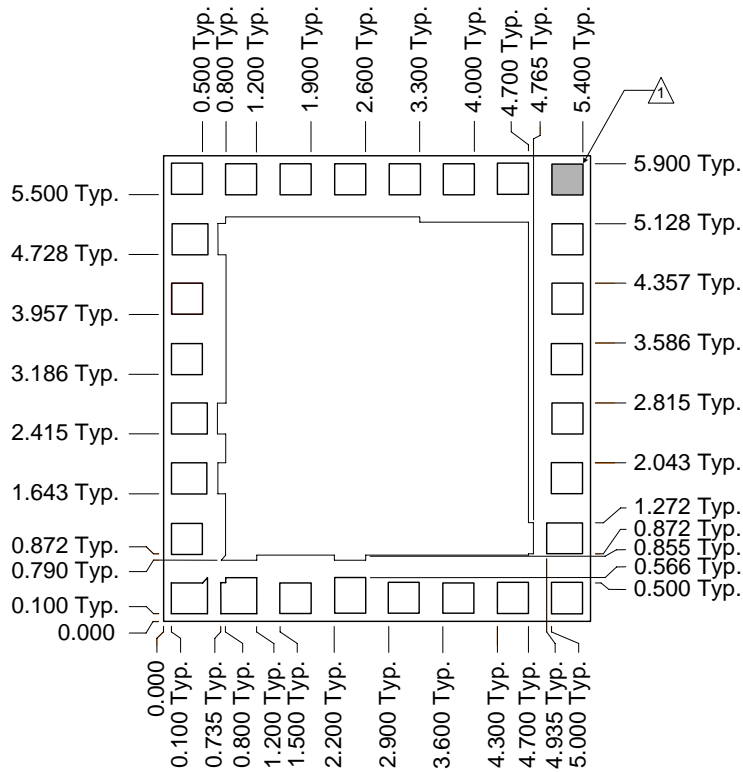
Pin	Function	Description	Interface Schematic
1	GND	Ground.	
2	RFIN_H	RF Input for the high band PA. This input is internally matched to 50Ω and AC coupled.	
3	VCC1B	First stage collector supply voltage.	
4	VCTRL	Analog bias control voltage used to reduce PA idle current and therefore improve efficiency at lower output power levels.	
5	GND	Ground.	
6	RFIN_L	RF Input for the low band PA. This input is internally matched to 50Ω and AC coupled.	
7	GND	Ground.	
8	VCC1A	First stage collector supply voltage.	
9	NC	No connection.	
10	VREF_L	Regulated voltage supply for amplifier bias circuit. Used to enable the low band PA.	
11	VCCBIAS_L	Power supply input for the DC bias circuitry. Must be $\geq 3.0V$ .	
12	GND	Ground.	
13	GND	Ground.	
14	GND	Ground.	
15	VCC2B	Output stage collector supply voltage. Refer to schematic for recommended bypassing.	
16	RFOUT_L	RF output for the low band PA. Internally AC coupled.	
17	GND	Ground.	
18	GND	Ground.	
19	GND	Ground.	
20	RFOUT_H	RF output for the high band PA. Internally AC coupled.	
21	GND	Ground.	
22	VCC2A	Output stage collector supply voltage. Refer to schematic for recommended bypassing.	
23	GND	Ground.	
24	GND	Ground.	
25	GND	Ground.	
26	GND	Ground.	
27	VREF_H	Regulated voltage supply for amplifier bias circuit. Used to enable the high band PA.	
28	VCCBIAS_H	Power supply input for the DC bias circuitry. Must be $\geq 3.0V$ .	
Pkg Base	GND	Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias. The pad should have a short thermal path to the ground plane.	

## Package Drawing

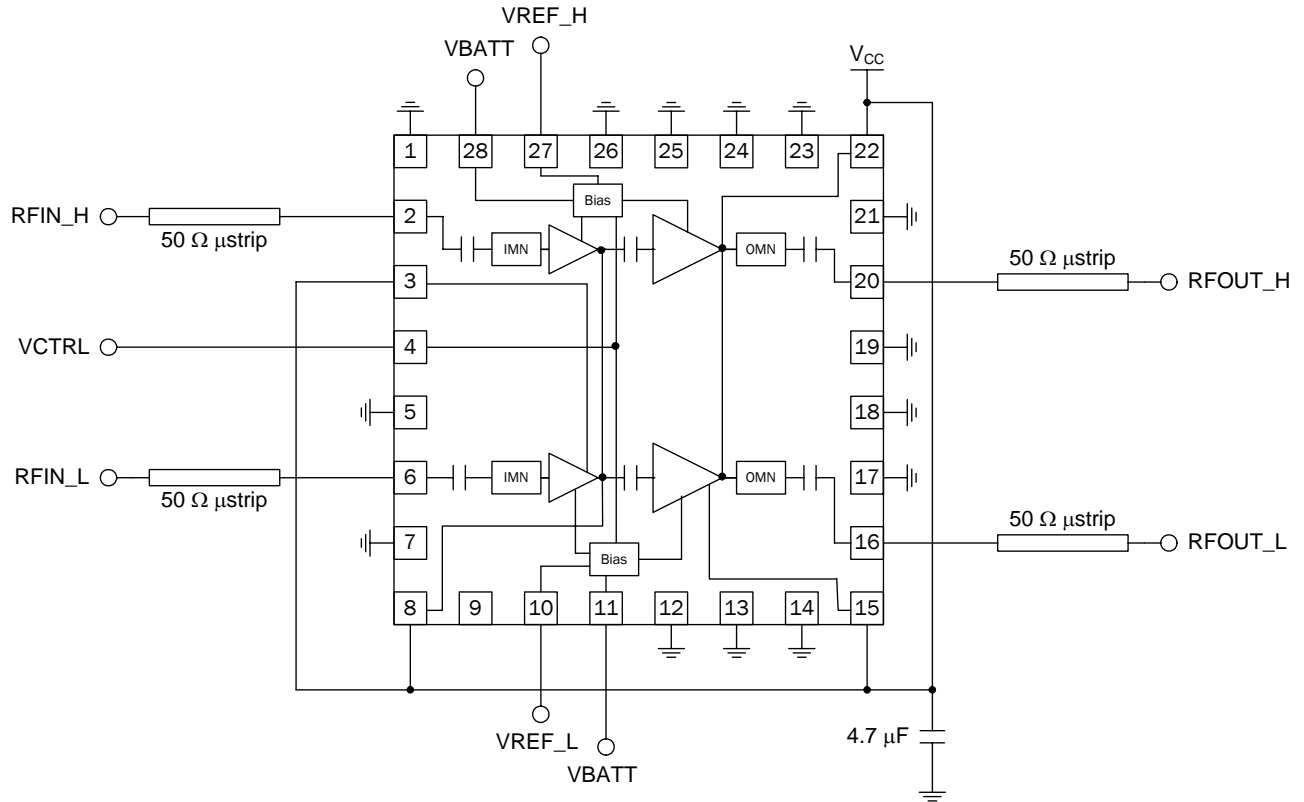


Shaded areas represent pin 1.

Dimensions in mm.



**Application Schematic**



## PCB Design Requirements

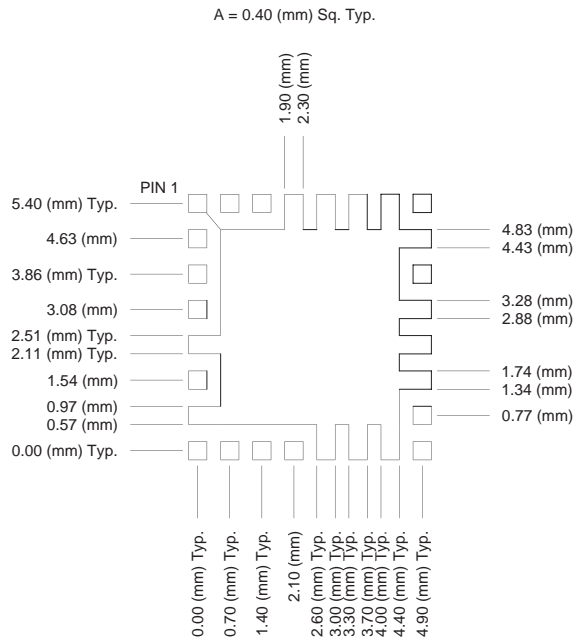
### PCB Surface Finish

The PCB surface finish used for RFMD's qualification process is electroless nickel, immersion gold. Typical thickness is 3 inch to 8 inch gold over 180 inch nickel.

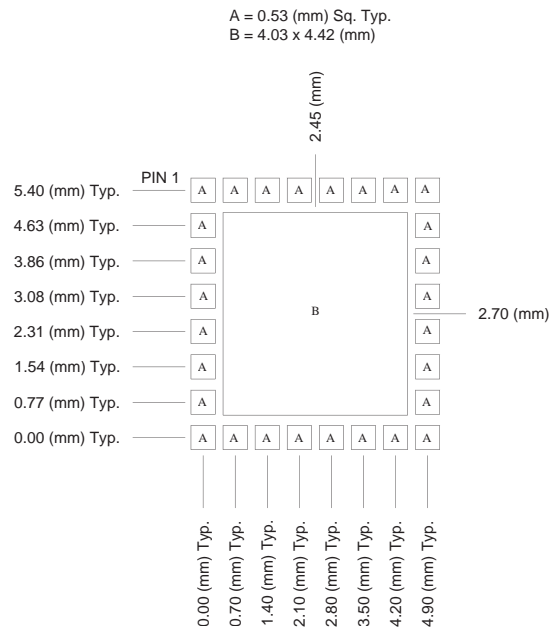
### PCB Land Pattern Recommendation \*

PCB land patterns for RFMD components are based on IPC-7351 standards and RFMD empirical data. The pad pattern shown has been developed and tested for optimized assembly at RFMD. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.

### PCB Metal Land and Solder Mask Pattern



RF6285 Metal Land Pattern



RF6285 Solder Mask Pattern

### Thermal Pad and Via Design

The PCB land pattern has been designed with a thermal pad that matches the exposed die paddle size on the bottom of the device.

Thermal vias are required in the PCB layout to effectively conduct heat away from the package. The via pattern has been designed to address thermal, power dissipation and electrical requirements of the device as well as accommodating routing strategies.

The via pattern used for the RFMD qualification is based on thru-hole vias with 0.203mm to 0.330mm finished hole size on a 0.5mm to 1.2mm grid pattern with 0.025mm plating on via walls. If micro vias are used in a design, it is suggested that the quantity of vias be increased by a 4:1 ratio to achieve similar results.